

ABSTRACT OF THE DISCLOSURE

An insulating gate type semiconductor device has a plurality of trench gate electrodes provided substantially in parallel. In this semiconductor device, among the trench gate electrodes, a thinning-out trench gate electrode excluding a channel-forming trench gate electrode is insulated from a gate wire and is connected to an emitter electrode or to a predetermined electric potential generating device for generating a negative electric potential with respect to an emitter potential. With this construction, a gate capacitance is decreased without drawbacks such as a decline of manufacturing yield and an increase in gate wire resistance, there are decreased oscillations of waveforms of voltage and current when in switching in the case of an element having a large area and operating the elements in parallel.

1005152-020402